

PN2369

NPN Switching Transistor

- This device is designed for high speed saturated switching at collector currents of 10mA to 100mA.
- Sourced from process 21.



Absolute Maximum Ratings* T_a =25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V _{CEO}	Collector-Emitter Voltage	15	V
V _{CBO}	Collector-Base Voltage	40	V
V _{EBO}	Emitter-Base Voltage	4.5	V
I _C	Collector Current - Continuous	200	mA
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 ~ 150	°C

^{*} This ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

These rating are based on a maximum junction temperature of 150 degrees C.
 These are steady limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics T_a=25°C unless otherwise noted

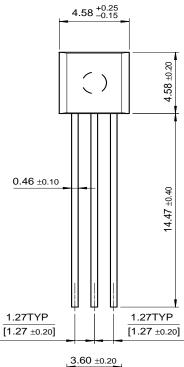
Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Charac	cteristics				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage *	$I_{C} = 10 \text{mA}, I_{B} = 0$	15		V
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	$I_C = 10\mu A, V_{BE} = 0$	40		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{C} = 10\mu A, I_{E} = 0$	40		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10\mu A, I_C = 0$	4.5		V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 20V, I_{E} = 0$ $V_{CB} = 20V, I_{E} = 0, T_{a} = 125^{\circ}C$		0.4 30	μA μA
On Charac	cteristics				
h _{FE}	DC Current Gain *	$I_C = 10 \text{mA}, V_{CE} = 1.0 \text{V}$ $I_C = 100 \text{mA}, V_{CE} = 2.0 \text{V}$	40 20	120	
V _{CE(sat)}	Collector-Emitter Saturation Voltage *	I _C = 10mA, I _B = 1.0mA		0.25	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 10mA, I _B = 1.0mA	0.7	0.85	V
Small Sigr	nal Characteristics				-
C _{obo}	Output Capacitance	$V_{CB} = 5.0V$, $I_{E} = 0$, $f = 1.0MHz$		4.0	pF
C _{ibo}	Input Capacitance	$V_{EB} = 0.5V, I_{C} = 0, f = 1.0MHz$		5.0	pF
h _{fe}	Small -Signal Current Gain	$I_C = 10 \text{mA}, V_{CE} = 10 \text{V}, R_G = 2.0 \text{k}\Omega,$ f = 100 MHz	5.0		
Switching	Characteristics				
t _s	Storage Time	$I_{B1} = I_{B2} = I_{C} = 10mA$		13	ns
t _{on}	Turn-On Time	$V_{CC} = 3.0V, I_{C} = 10mA, I_{B1} = 3.0mA$		12	ns
t _{off}	Turn-Off Time	$V_{CC} = 3.0V, I_C = 10mA, I_{B1} = 3.0mA,$ $I_{B2} = 1.5mA$		18	ns

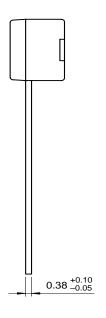
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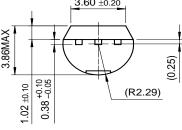
Thermal Characteristics T _a =25°C unless otherwise noted			
Symbol	Parameter	Max.	Units
P _D	Total Device Dissipation Derate above 25°C	350 2.8	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

Package Dimensions

TO-92







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